

## N-Channel 60V (D-S) Power MOSFET

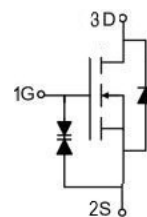
### Features

- 100% Avalanche Tested
- Halogen Free, Pb-Free
- RoHS Compliant



### Applications

- Relay driver
- Switching circuits
- High-side load switch
- High-speed line driver



### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain Source Voltage	$V_{DS}$	60	V
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current, Continuous $V_{GS}=10\text{V}$	$I_D$	0.3	A
Drain Current, Pulsed (Note 1)	$I_{DM}$	0.8	A
Power Dissipation	$P_D$	0.36	W
Operating Junction/Storage Temperature Range	$T_J/T_{STG}$	-55 to +150	$^\circ\text{C}$

Note 1: Single pulse;  $t_p \leq 1\mu\text{s}$ .

### Thermal Characteristics

Parameter	Symbol	Max	Unit
Thermal Resistance Junction to Ambient (Note 2)	$R_{thJA}$	350	$^\circ\text{C/W}$

Note 2: Device mounted on 1 square inch FR4 PCB board, with 2oz single-sided copper, in a  $25^\circ\text{C}$  still air environment.

## Electrical Characteristics (T<sub>A</sub> =25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	--	--	1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA	1	--	2.5	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	--	--	±150	nA
Drain Source On-state Resistance (Note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A	--	--	3.5	Ω
		V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A	--	--	3	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, R <sub>L</sub> =150Ω, R <sub>G</sub> =10Ω	--	--	25	ns
Turn-off Delay Time	t <sub>d(off)</sub>		--	--	35	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	--	30	--	pF
Output Capacitance	C <sub>oss</sub>		--	6	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	3	--	

## Reverse Diode Characteristics (T<sub>A</sub> =25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Current, Continuous	I <sub>SD</sub>	T <sub>A</sub> =25°C	--	--	0.3	A
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	I <sub>F</sub> =0.2A, V <sub>GS</sub> =0V	--	--	1.3	V

Note 3: Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.

## Typical Characteristics Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 - Output Characteristics

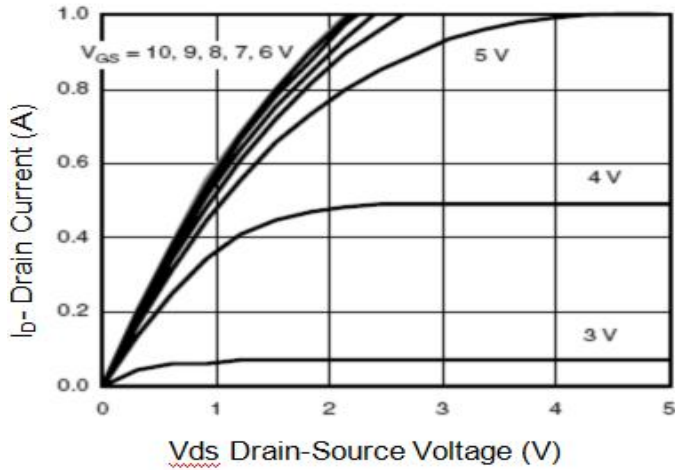


Fig. 2 - Transfer Characteristics

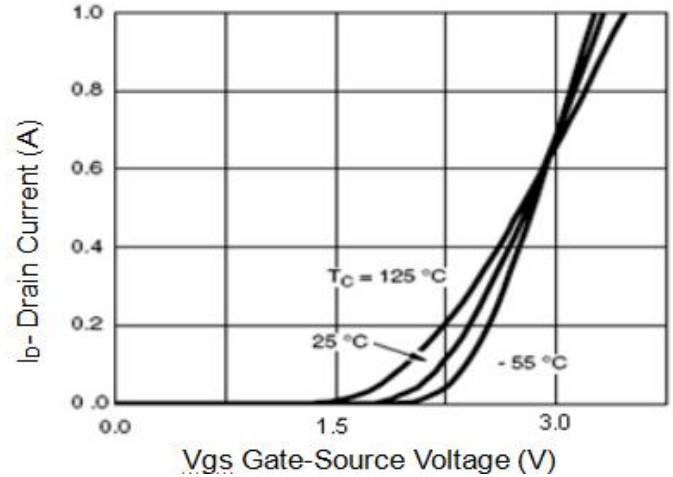


Fig. 3 - Drain-Source On-Resistance

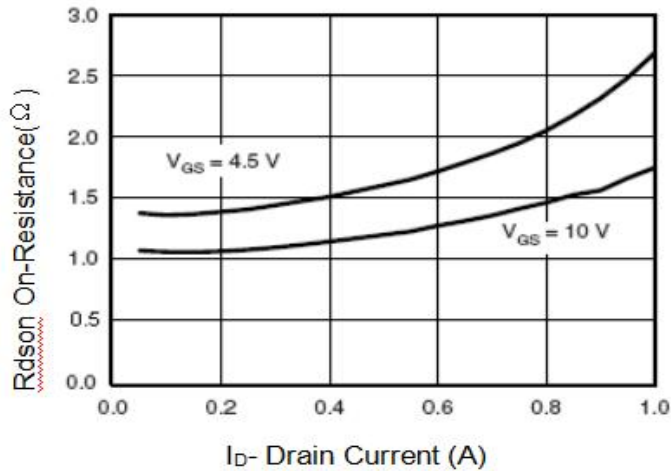


Fig. 4 - Normalized On-Resistance

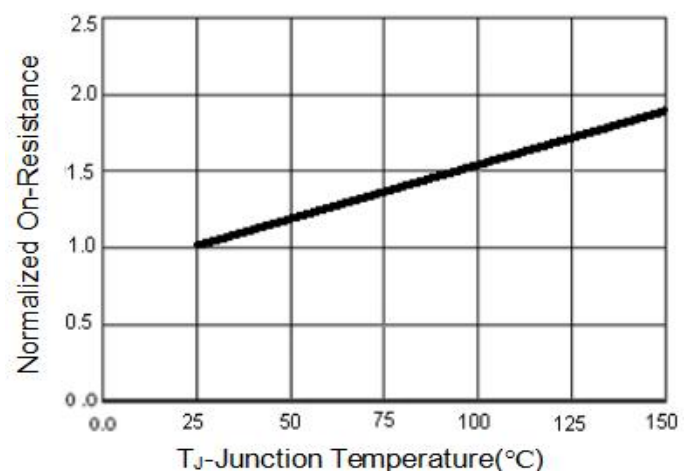


Fig. 5 - Capacitance

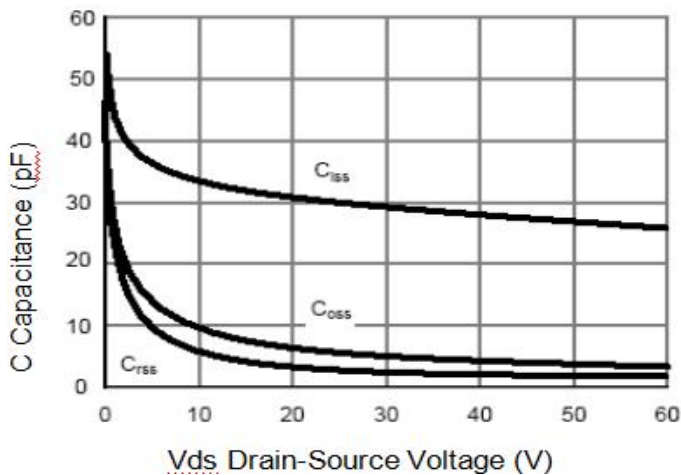
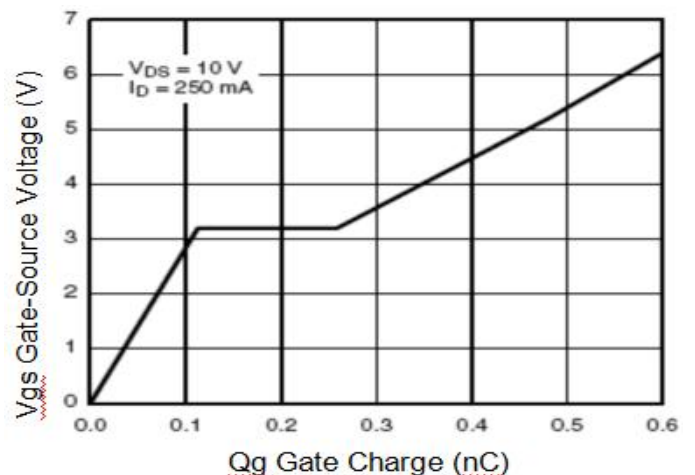


Fig. 6 - Gate Charge



## Typical Characteristics Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig.7 - Maximum Transient Thermal Impedance, Junction-Ambient

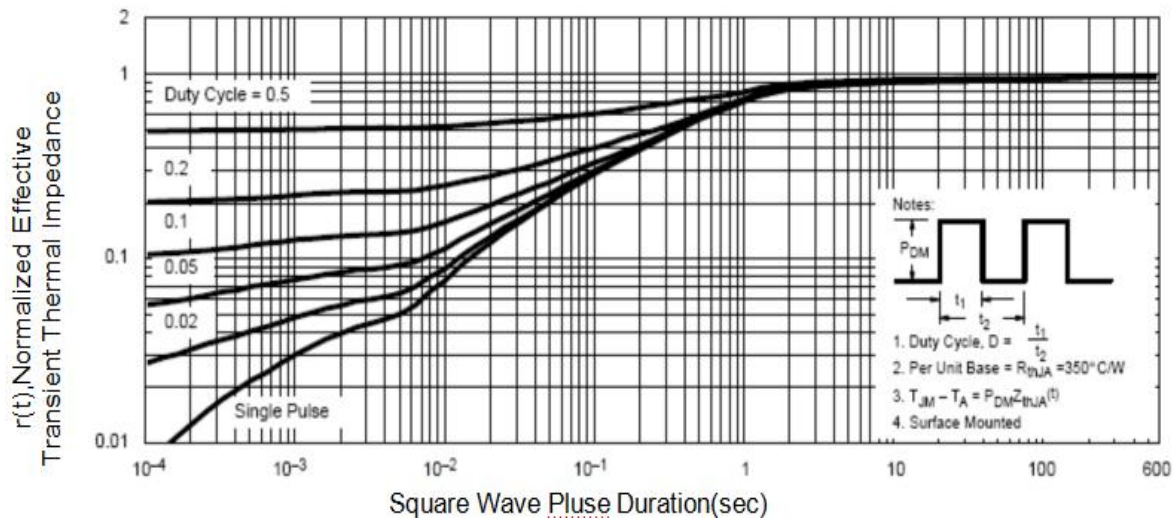
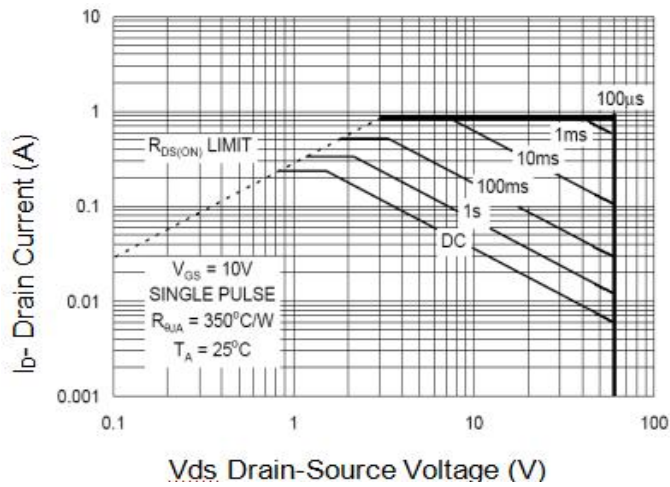
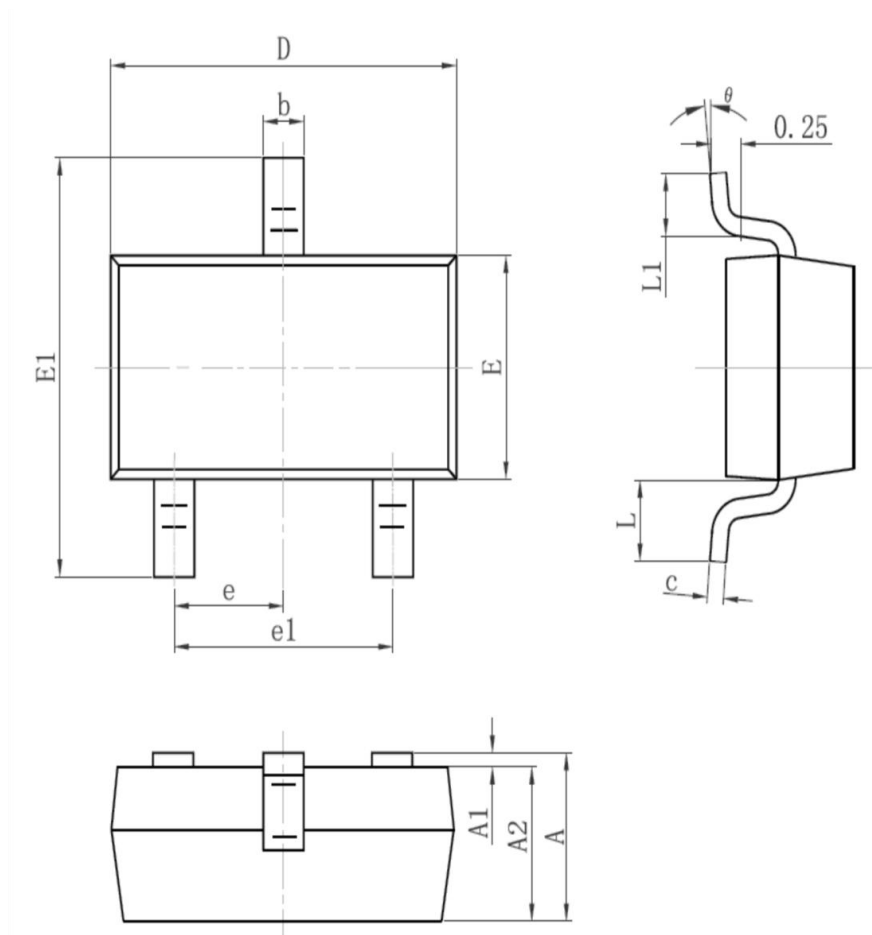


Fig. 8 - Safe Operating Area



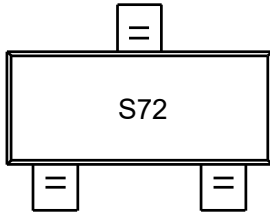
## Package Outline Dimensions (Unit: millimeters)

### SOT-23



Symbol	Dimension In Millimeters		Dimension In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.95TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.55REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## Marking Outline



Part Name: 2N7002K

1. P/N Mark: S72

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